



# FDMS3572

## N-Channel UltraFET Trench® MOSFET

80V, 22A, 16.5mΩ

### Features

- Max  $r_{DS(on)}$  = 16.5mΩ at  $V_{GS}$  = 10V,  $I_D$  = 8.8A
- Max  $r_{DS(on)}$  = 24mΩ at  $V_{GS}$  = 6V,  $I_D$  = 8.4A
- Typ  $Q_g$  = 28nC at  $V_{GS}$  = 10V
- Low Miller Charge
- Optimized efficiency at high frequencies
- RoHS Compliant

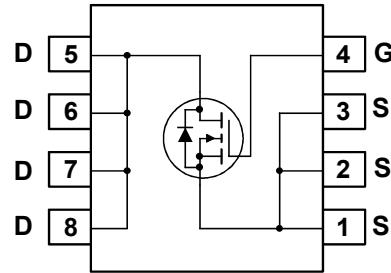
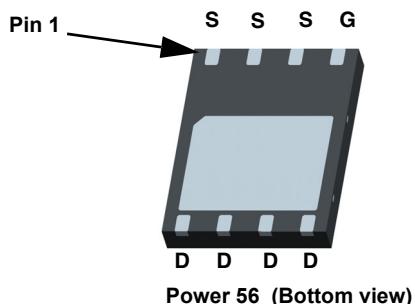


### General Description

UltraFET devices combine characteristics that enable benchmark efficiency in power conversion applications. Optimized for  $r_{DS(on)}$ , low ESR, low total and Miller gate charge, these devices are ideal for high frequency DC to DC converters.

### Application

- DC - DC Conversion



### MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain to Source Voltage	80	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous (Package limited) $T_C = 25^\circ\text{C}$	22	A
	-Continuous (Silicon limited) $T_C = 25^\circ\text{C}$	48	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	8.8	
	-Pulsed	50	
$P_D$	Power Dissipation $T_C = 25^\circ\text{C}$	78	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.6	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS3572	FDMS3572	Power 56	7"	12mm	3000 units

**Electrical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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**Off Characteristics**

$\text{BV}_{\text{DSS}}$	Drain to Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	80			V
$\frac{\Delta \text{BV}_{\text{DSS}}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		76		$\text{mV}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{DS} = 64\text{V}, V_{GS} = 0\text{V}$			1	$\mu\text{A}$
$I_{\text{GSS}}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			$\pm 100$	nA

**On Characteristics**

$V_{GS(\text{th})}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	2	3.2	4	V
$\frac{\Delta V_{GS(\text{th})}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\mu\text{A}$ , referenced to $25^\circ\text{C}$		-11		$\text{mV}/^\circ\text{C}$
$r_{DS(\text{on})}$	Drain to Source On Resistance	$V_{GS} = 10\text{V}, I_D = 8.8\text{A}$		13.5	16.5	$\text{m}\Omega$
		$V_{GS} = 6\text{V}, I_D = 8.4\text{A}$		18.3	24	
		$V_{GS} = 10\text{V}, I_D = 8.8\text{A}, T_J = 125^\circ\text{C}$		22.2	29	
$g_{\text{FS}}$	Forward Transconductance	$V_{DS} = 10\text{V}, I_D = 8.8\text{A}$		23		s

**Dynamic Characteristics**

$C_{\text{iss}}$	Input Capacitance	$V_{DS} = 40\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$		1870	2490	pF
$C_{\text{oss}}$	Output Capacitance			275	365	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance			78	120	pF
$R_g$	Gate Resistance	$f = 1\text{MHz}$		1.3		$\Omega$

**Switching Characteristics**

$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{DD} = 40\text{V}, I_D = 8.8\text{A}$ $V_{GS} = 10\text{V}, R_{\text{GEN}} = 6\Omega$		11	20	ns
$t_r$	Rise Time			13	24	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time			24	39	ns
$t_f$	Fall Time			12	22	ns
$Q_{\text{g(TOT)}}$	Total Gate Charge at 10V	$V_{GS} = 0\text{V to } 10\text{V}$ $V_{DD} = 40\text{V}$ $I_D = 8.8\text{A}$		28	40	nC
$Q_{\text{gs}}$	Gate to Source Gate Charge			9		nC
$Q_{\text{gd}}$	Gate to Drain "Miller" Charge			8		nC

**Drain-Source Diode Characteristics**

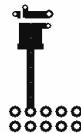
$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{V}, I_S = 8.8\text{A}$ (Note 2)		0.8	1.2	V
$t_{\text{rr}}$	Reverse Recovery Time	$I_F = 8.8\text{A}, di/dt = 100\text{A}/\mu\text{s}$		43	65	ns
$Q_{\text{rr}}$	Reverse Recovery Charge				71	107

**Notes:**

1:  $R_{\text{QJA}}$  is determined with the device mounted on a  $1\text{in}^2$  pad 2 oz copper pad on a  $1.5 \times 1.5$  in. board of FR-4 material.  $R_{\text{QJC}}$  is guaranteed by design while  $R_{\text{QCA}}$  is determined by the user's board design.



a.  $50^\circ\text{C}/\text{W}$  when mounted on a  $1\text{in}^2$  pad of 2 oz copper



b.  $125^\circ\text{C}/\text{W}$  when mounted on a minimum pad of 2 oz copper

2: Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty cycle  $< 2.0\%$ .

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

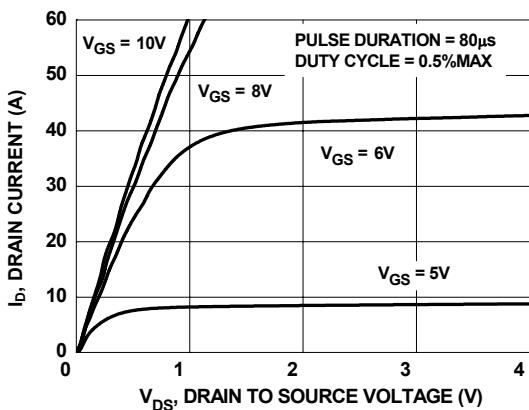


Figure 1. On Region Characteristics

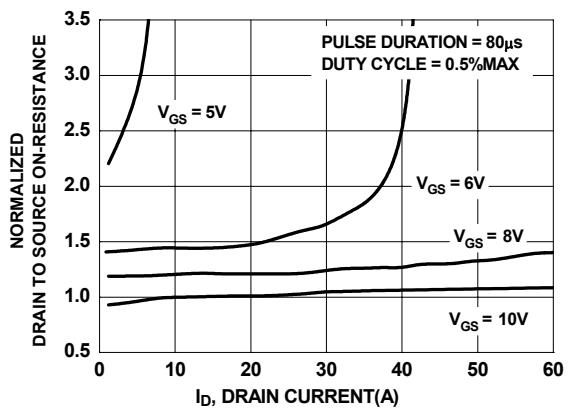


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

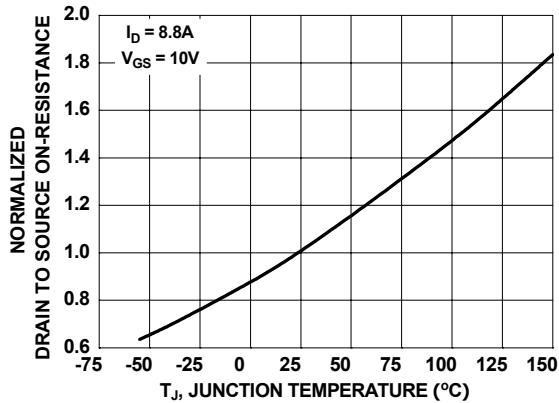


Figure 3. Normalized On Resistance vs Junction Temperature

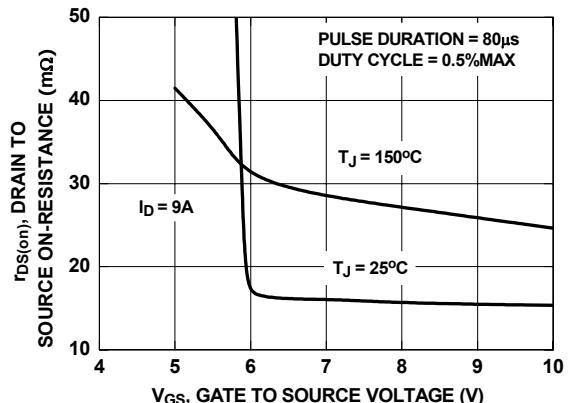


Figure 4. On-Resistance vs Gate to Source Voltage

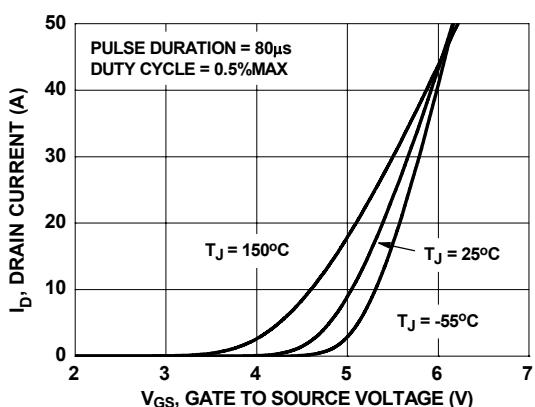


Figure 5. Transfer Characteristics

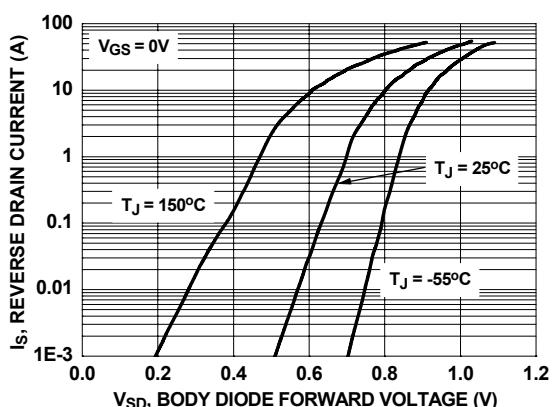


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

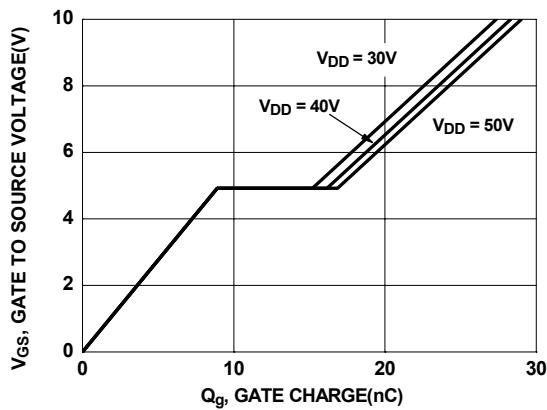


Figure 7. Gate Charge Characteristics

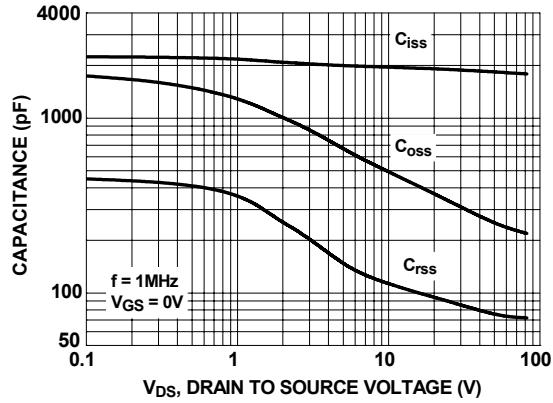


Figure 8. Capacitance vs Drain to Source Voltage

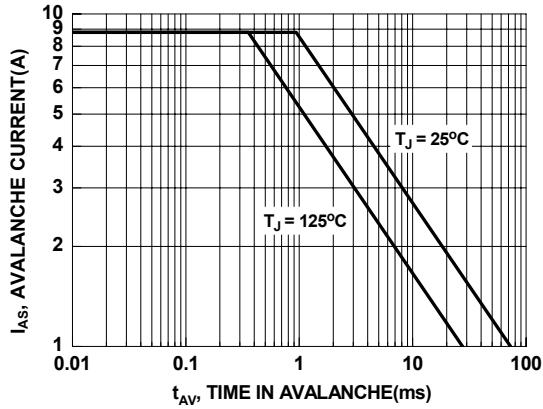


Figure 9. Unclamped Inductive Switching Capability

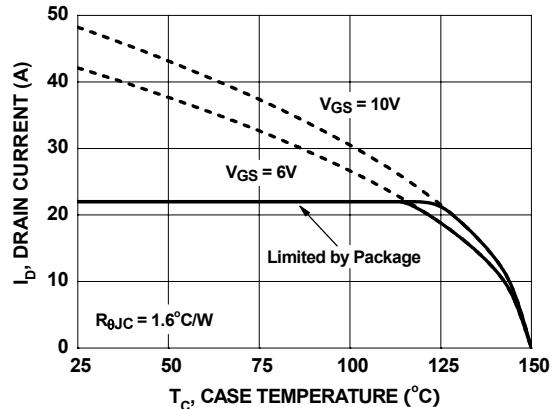


Figure 10. Maximum Continuous Drain Current vs Case Temperature

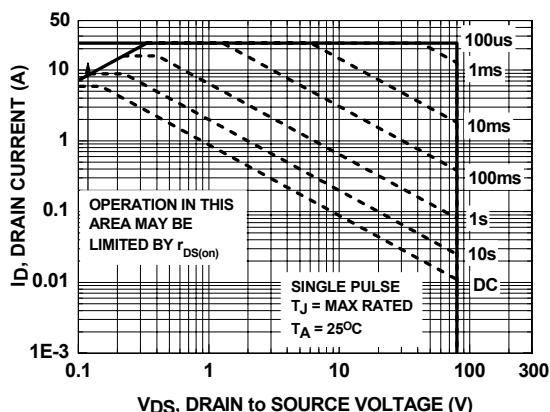


Figure 11. Forward Bias Safe Operating Area

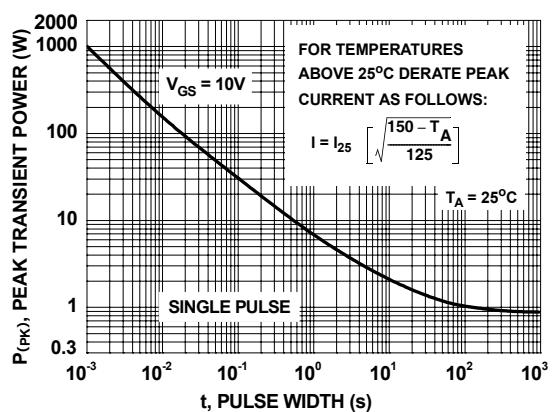


Figure 12. Single Pulse Maximum Power Dissipation

**Typical Characteristics**  $T_J = 25^\circ\text{C}$  unless otherwise noted

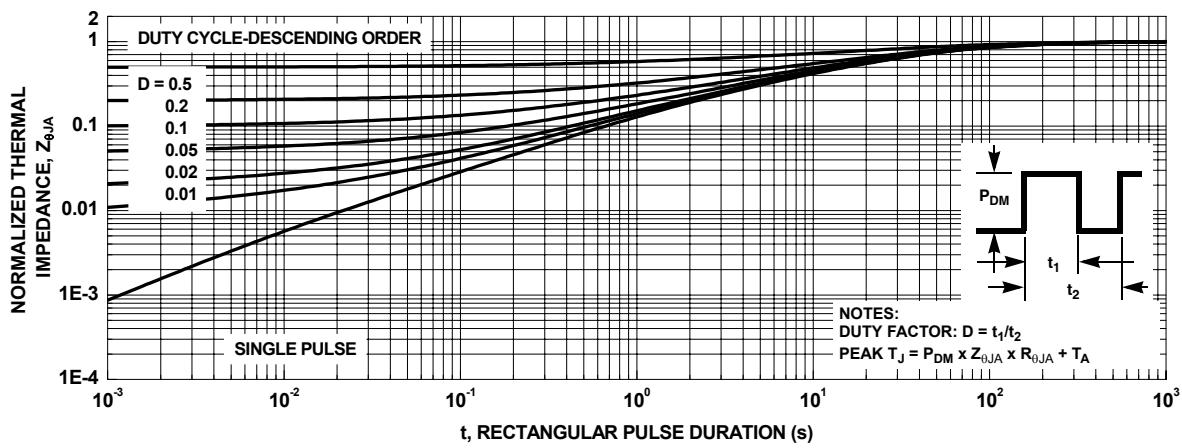
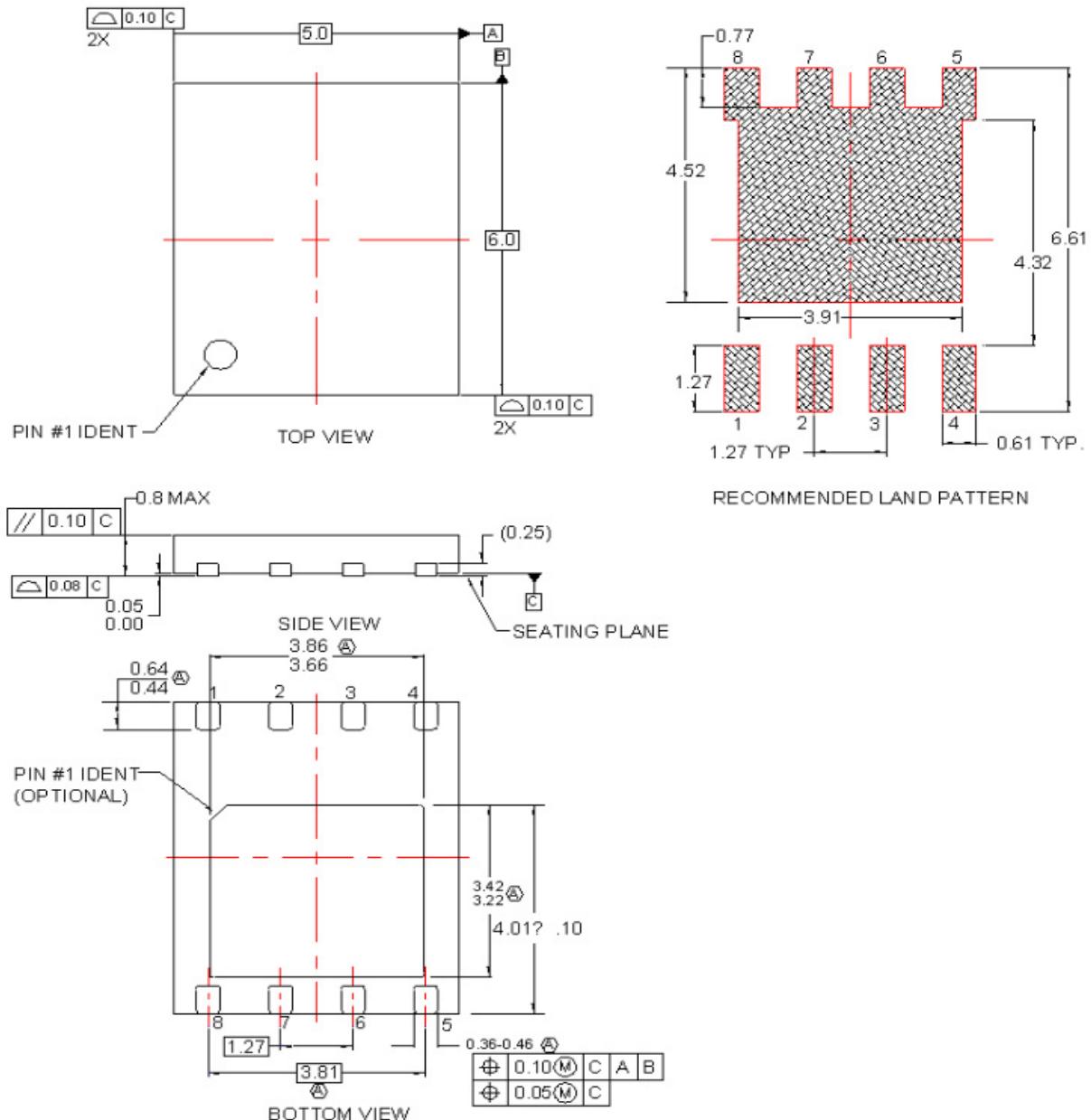


Figure 13. Transient Thermal Response Curve

# FDMS3572 N-Channel UltraFET<sup>®</sup> Trench<sup>®</sup> MOSFET



## NOTES:

- (A) DOES NOT FULLY CONFORM TO JEDEC REGISTRATION, MO-229. DATED 11/2001.
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- D. TERMINALS 5,6,7 AND 8 ARE TIED TO THE EXPOSED PADDLE

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Datasheet Identification	Product Status	Definition
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